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(54) Title: VERTICAL TRANSISTOR PHASE CHANGE MEMORY

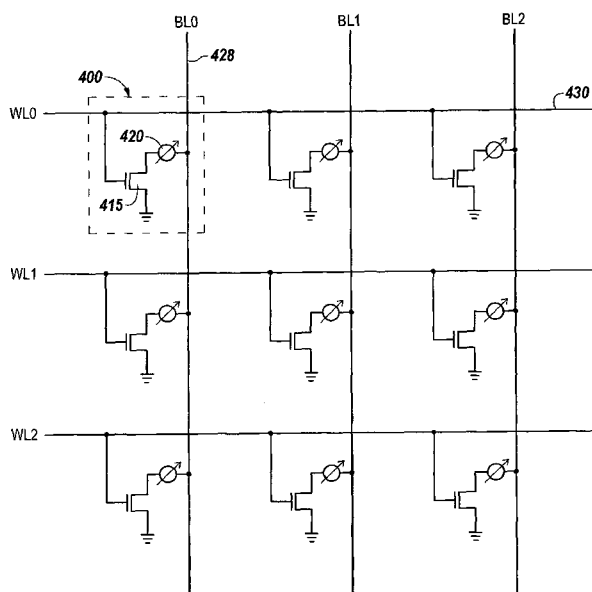


Fig. 4

(57) Abstract: Vertical transistor phase change memory and methods of processing phase change memory are described herein. One or more methods include forming a dielectric on at least a portion of a vertical transistor, forming an electrode on the dielectric, and forming a vertical strip of phase change material on a portion of a side of the electrode and on a portion of a side of the dielectric extending along the electrode and the dielectric into contact with the vertical transistor.